

# **ST730A**

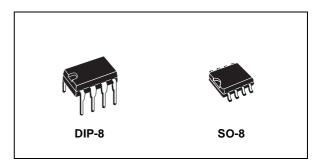
# 5V STEP-DOWN, CURRENT-MODE PWM DC-DC CONVERTERS

- **UP TO 450mA LOAD CURRENTS**
- 200kHz HIGH-FREQUENCY CURRENT-MODE PWM
- 85% TO 96% EFFICIENCIES
- 33µH OR 100µH PRE-SELECTED INDUCTOR VALUE, NO COMPONENT **DESIGN REQUIRED**
- 0.8mA QUIESCENT CURRENT .
- 0.3µA SHUTDOWN SUPPLY CURRENT
- ADJUSTABLE OUTPUT VOLTAGE
- OVERCURRENT, SOFT-START AND UNDERVOLTAGE LOCKOUT PROTECTION
- CYCLE-BY-CYCLE CURRENT LIMITING .
- PACKAGE AVAILABLE: DIP-8 AND SO-8

#### DESCRIPTION

The ST730A is a 5V output CMOS, step-down switching regulator. The ST730A accepts inputs between 5.2V and 11V and delivers 450mA. Typical efficiencies are 85% to 96%.

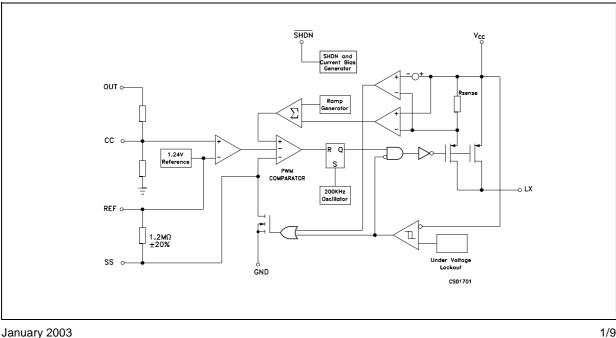
Quiescent supply current is 0.8mA and only 0.3µA in shutdown mode. The output does not exhibit frequency over this specified range. Pulse-width modulation (PWM) current-mode control provides



precise output regulation and excellent transient responses. Output voltage accuracy is guaranteed to be ±5% over line, load, and temperature varations.

Fixed-frequency switching and absence of subharmonic ruipple allows easy filtering of output ripple and noise, as well as the use of small external components. This regulators require only single inductor value to work in most а applications, so no inductor design is necessary. Typical applications are: Cellular phones & radios, portable Instruments, Portable Communications Equipments and Computer Peripherals.

#### SCHEMATIC DIAGRAM



# **ABSOLUTE MAXIMUM RATINGS**

Symbol	Parameter <sup>2</sup>	Value	Unit
V <sub>CC</sub>	DC Input Voltage	-0.3 to 12	V
$V_{LX}$	Switch Pin Voltage	-0.3 to (V <sub>CC</sub> + 0.3)	V
V <sub>SHDN</sub>	Shutdown Voltage (SHDN)	-0.3 to (V <sub>CC</sub> + 0.3)	V
V <sub>S</sub> ,V <sub>C</sub>	Soft Start (SS) and Compensation Capacitor (CC) Pins Voltage	-0.3 to (V <sub>CC</sub> + 0.3)	V
I <sub>LX</sub>	Switching Peak Current	2	А
I <sub>REF</sub>	Reference Current	2.5	mA
P <sub>TOT</sub>	Continuous Power Dissipation at T <sub>A</sub> =70°C (DIP-8) (SO-8)	550 344	mW mW
T <sub>stg</sub>	Storage Temperature Range	-40 to +150	°C
T <sub>op</sub>	Operating Junction Temperature Range (C series) (B series)	0 to +70 -40 to +85	℃ ℃

Absolute Maximum Ratings are those values beyond which damage to the device may occur. Functional operation under these condition is not implied.

# THERMAL DATA

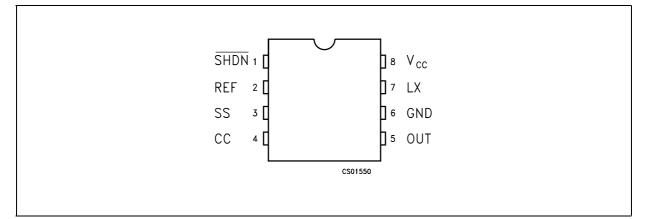
Symbol	Parameter	SO-8	DIP-8	Unit
R <sub>thj-amb</sub>	Thermal Resistance Junction-ambient (*)	160	100	°C/W

 $(\ensuremath{^*})$  This value depends from thermal design of PCB on which the device is mounted.

### **ORDERING CODES**

ТҮРЕ	DIP8	SO-8	SO-8 (T&R)
ST730AB	ST730ABN	ST730ABD	ST730ABD-TR
ST730AC	ST730ACN	ST730ACD	ST730ACD-TR

# **CONNECTION DIAGRAM** (top view)



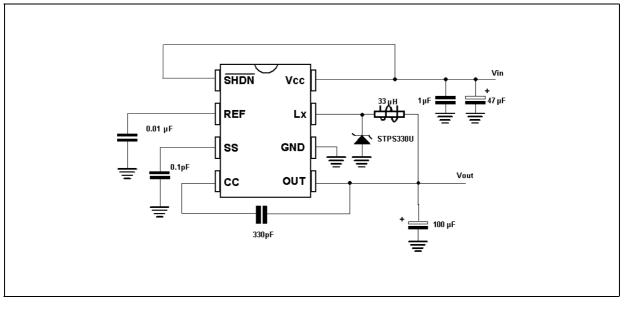
# **PIN DESCRIPTION**

Pin N°	Symbol	Name and Function
1	SHDN	Shutdown control (active low): If connected to GND the IC is in shutdown. Connect to $V_{CC}$ for normal operation (ON MODE)
2	REF	Reference Output Voltage: (1.25V): Bypass to GND with a capacitor that does not exceed 47nF
3	SS	Soft Start: a capacitor between SS and GND provides soft-start and short-circuit protections.
4	СС	Compensation Capacitor Input: externally compensates the outer (voltage) feedback loop. Connect to OUT with 330pF capacitor
5	OUT	Output Voltage Sense Input: provides regulation of feedback sensing. Connect to 5V output.
6	GND	Ground
7	LX	Switch Output. Drain of internal P-Channel Power MOSFET
8	V <sub>CC</sub>	Supply Voltage Input. Bypass to GND with 1µF ceramic capacitance and large value electrolytic capacitor in parallel. The 1µF capacitor must be as close as possible to the GND and V <sub>CC</sub> pins

Symbol	Parameter	Test Conditions	Min.	Тур.	Max.	Unit
V <sub>CC</sub>	Input Voltage		4		11	V
Vo	Output Voltage	$V_{CC} = 6 \text{ to } 11 \text{V}$ $I_{O} = 0 \text{ to } 450 \text{mA}$	4.75	5	5.25	V
$\Delta V_O$	Line Regulation	V <sub>CC</sub> = 5.2 to 11V		0.15		%/V
$\Delta V_O$	Load Regulatio	I <sub>O</sub> = 0 to 450mA		0.005		%/mA
η	Power Efficency	I <sub>O</sub> =300mA		92		%
I <sub>SUPPLY</sub>	Supply Current	ON Mode OFF Mode, SHDN=0		0.8 0.3	2.5 100	mA μA
V <sub>IH</sub>	SHDN Input High Threshold		2			V
V <sub>IL</sub>	SHDN Input Low Threshold				0.25	V
I <sub>SHDN</sub>	Shutdown Input Leakage Current				1	μΑ
V <sub>LOCK</sub>	Under Voltage Lockout	V <sub>CC</sub> Falling		2.7	3	V
R <sub>DS(on)</sub>	LX On Resistance	I <sub>LX</sub> =500mA		0.5		Ω
I <sub>LX</sub>	LX Leakage Current	$V_{CC} = 12V$ $V_{LX} = 0V$		1		μA
$V_{REF}$	Reference Voltage	$T_A = 25^{\circ}C$	1.17	1.24	1.31	V
$\Delta V_{REF}$	Temperature Reference Drift			50		ppm/°C
f <sub>OSC</sub>	Switching Frequency	B series C series	180 160	200	220 280	KHz
R <sub>C</sub>	Compensation Pin Impedance			7500		Ω

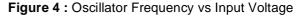
# $\textbf{ELECTRICAL CHARACTERISTICS} (V_{CC} = 5V, I_{O} = 0mA, T_{A} = T_{MIN} \text{ to } T_{MAX}, \text{ unless otherwise specified.})$

# **TYPICAL APPLICATION CIRCUIT**



# TYPICAL PERFORMANCE CHARACTERISTICS (unless otherwise specified T<sub>i</sub> = 25°C

Figure 1 : Efficency vs Output Current



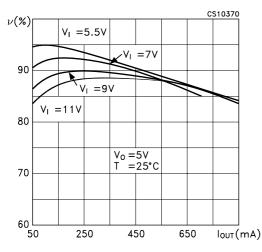


Figure 2 : Supply Current vs Temperature

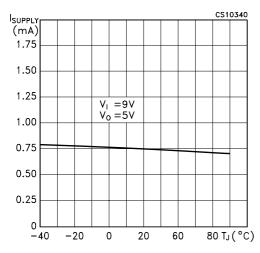
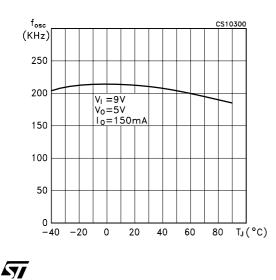
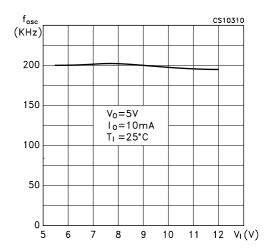
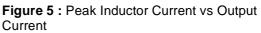


Figure 3 : Oscillator Frequency vs Temperature







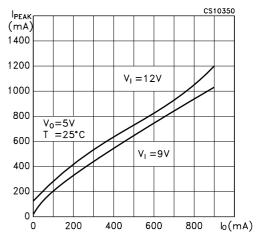


Figure 6 : Output Voltage vs Output Current

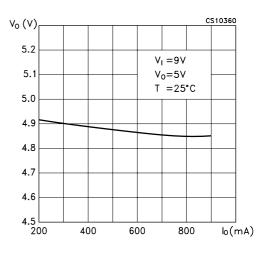


Figure 7 : Switching Waveforms, Continuous Conduction

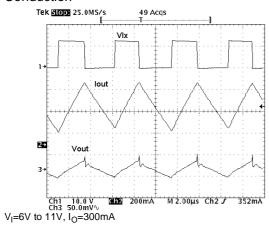
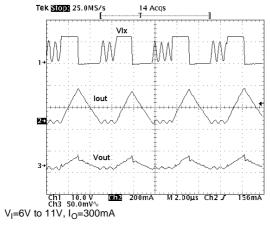


Figure 8 : Switching Waveforms, Discontinuous Conduction



### Figure 9 : Line Transient

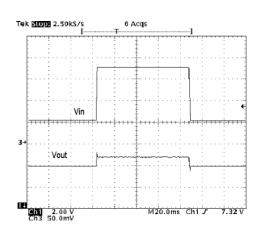
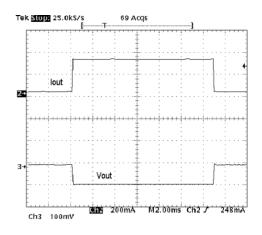
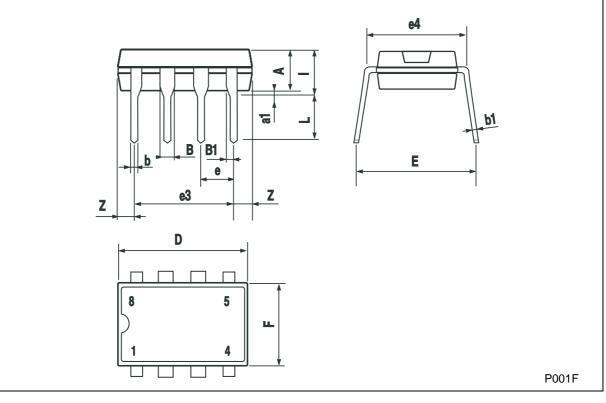


Figure 10 : Load Transient



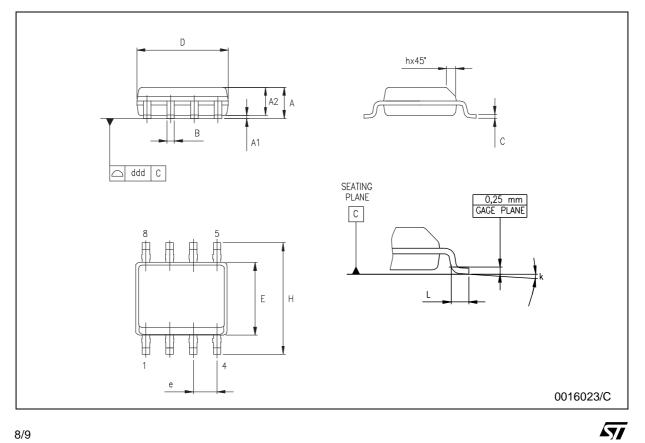
DIM.		mm.		inch		
	MIN.	ТҮР	MAX.	MIN.	TYP.	MAX.
А		3.3			0.130	
a1	0.7			0.028		
В	1.39		1.65	0.055		0.065
B1	0.91		1.04	0.036		0.041
b		0.5			0.020	
b1	0.38		0.5	0.015		0.020
D			9.8			0.386
Е		8.8			0.346	
е		2.54			0.100	
e3		7.62			0.300	
e4		7.62			0.300	
F			7.1			0.280
I			4.8			0.189
L		3.3			0.130	
Z	0.44		1.6	0.017		0.063





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	SO-8 MECHANICAL DATA						
DIM	mm.			inch			
DIM.	MIN.	TYP	MAX.	MIN.	TYP.	MAX.	
А	1.35		1.75	0.053		0.069	
A1	0.10		0.25	0.04		0.010	
A2	1.10		1.65	0.043		0.065	
В	0.33		0.51	0.013		0.020	
С	0.19		0.25	0.007		0.010	
D	4.80		5.00	0.189		0.197	
Е	3.80		4.00	0.150		0.157	
е		1.27			0.050		
Н	5.80		6.20	0.228		0.244	
h	0.25		0.50	0.010		0.020	
L	0.40		1.27	0.016		0.050	
k	8° (max.)						
ddd			0.1			0.04	



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